



9/Amend C
5/28/03
C.P.

Docket No.: M4065.0151/P151-B
(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:
Vishnu K. Agarwal, et al.

M. Brauns
7/1/03

Application No.: 09/930,958

Group Art Unit: 2814

Filed: August 17, 2001

Examiner: Theresa T. Doan

For: MULTILAYER ELECTRODE FOR A
FERROELECTRIC CAPACITOR

AMENDMENT UNDER 37 CFR § 1.116

DO NOT ENTER

TO
06/02/03

MAIL STOP: AF
Commissioner for Patents
P.O. Box 1450
Washington, DC 22313-1450

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MAY 23 2003
TECHNOLOGY CENTER 2800

Dear Sir:

Responsive to the Office Action dated February 27, 2003, please amend the
above-captioned application as follows:

IN THE CLAIMS:

Please cancel claim 60.

Please rewrite claim 125 as follows:

125. (amended) A memory cell, comprising:

a substrate;

a transistor including a gate on said substrate and a source/drain region in said
substrate disposed adjacent to said gate;

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